

P-Channel 20 V (D-S) MOSFET

DESCRIPTION

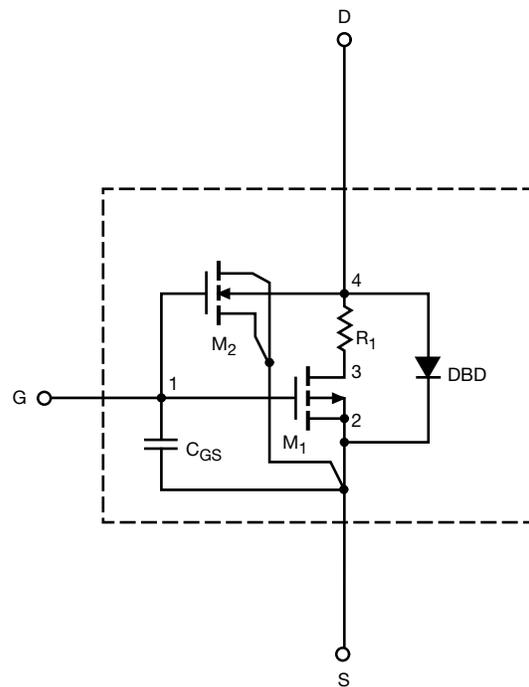
The attached SPICE model describes the typical electrical characteristics of the p-channel vertical DMOS. The subcircuit model is extracted and optimized over the -55 °C to 125 °C temperature ranges under the pulsed 0 V to 5 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- P-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the -55 °C to +125 °C Temperature Range
- Model the Gate Charge

SUBCIRCUIT MODEL SCHEMATIC



Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



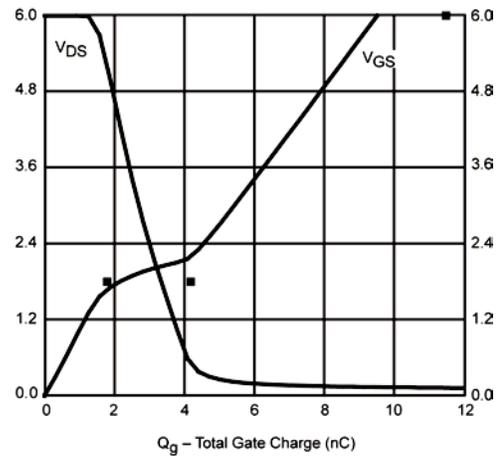
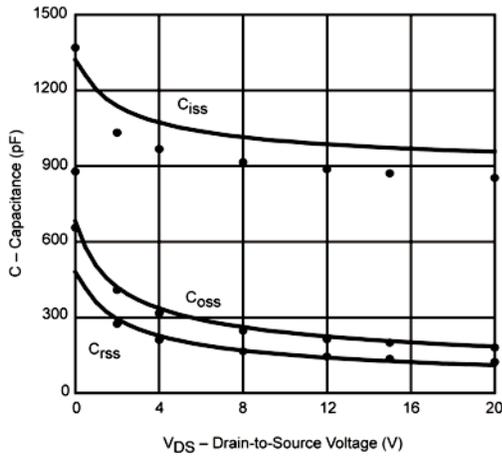
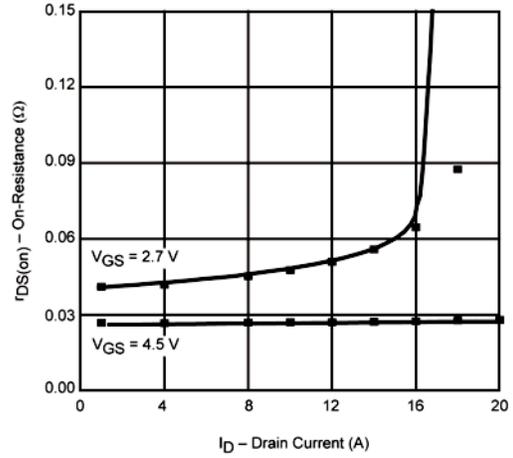
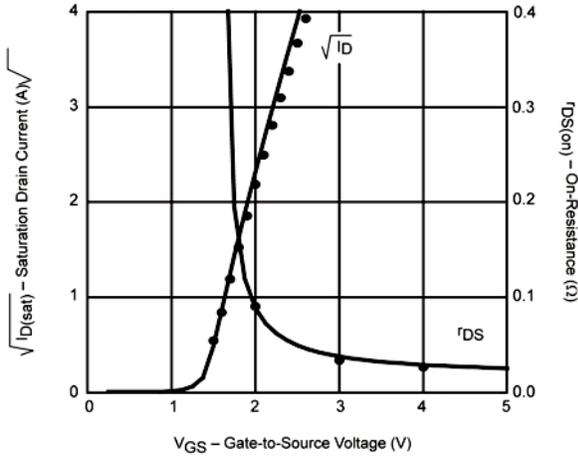
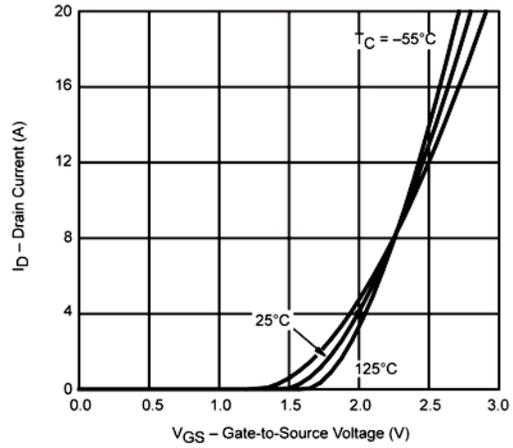
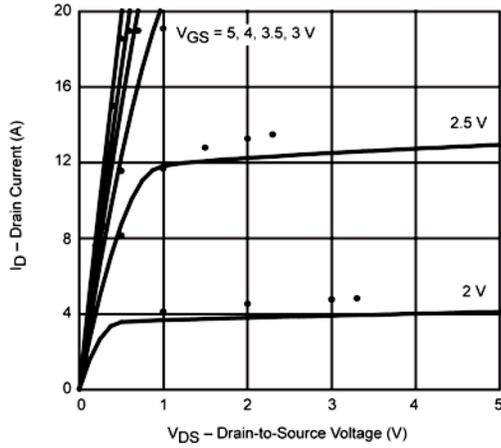
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	1.2	-	V
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\ \text{V}, V_{GS} = -4.5\ \text{V}$	78	-	A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\ \text{V}, I_D = -6.2\ \text{A}$	0.026	0.030	Ω
		$V_{GS} = -2.7\ \text{V}, I_D = -5\ \text{A}$	0.043	0.050	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\ \text{V}, I_D = -6.2\ \text{A}$	13	15	S
Diode Forward Voltage	V_{SD}	$I_S = -2.6\ \text{A}, V_{GS} = 0\ \text{V}$	-0.82	-0.76	V
Dynamic^b					
Total Gate Charge	Q_g	$V_{DS} = -6\ \text{V}, V_{GS} = -4.5\ \text{V}, I_D = -6.2\ \text{A}$	8	8.8	nC
Gate-Source Charge	Q_{gs}		1.8	1.8	
Gate-Drain Charge	Q_{gd}		2.4	2.4	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -6\ \text{V}, R_L = 6\ \Omega$ $I_D = -1\ \text{A}, V_{GEN} = -4.5\ \text{V}, R_g = 6\ \Omega$	58	40	ns
Rise Time	t_r		29	55	
Turn-Off Delay Time	$t_{d(off)}$		58	65	
Fall Time	t_f		18	30	

Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\ \%$.
b. Guaranteed by design, not subject to production testing.



COMPARISON OF MODEL WITH MEASURED DATA ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Note

- Dots and squares represent measured data.